

isc N-Channel MOSFET Transistor

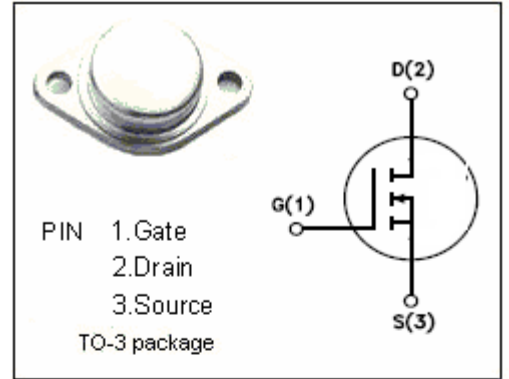
2N6756

DESCRIPTION

- VGS Rated at $\pm 20V$
- Silicon Gate for fast switching speeds
- I_{DSS} 、 $R_{DS(ON)}$,specified at elevated temperature
- Low drive requirements

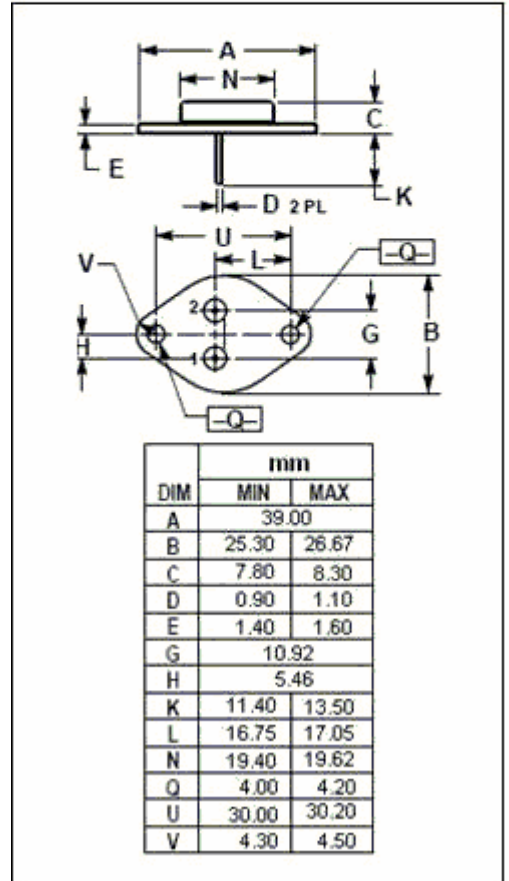
APPLICATIONS

designed for high power ,high speed application ,such as switching applies,UPS,AC and DC motor controls , relay and high energy pulse circuits.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=37^\circ C$	14	A
P_{tot}	Total Dissipation@ $TC=25^\circ C$	75	W
T_j	Max. Operating Junction Temperature	-55~150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	1.67	$^\circ C/W$

isc N-Channel Mosfet Transistor**2N6756****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	100		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 9A		0.18	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = 20V; V _{DS} = 0		100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V; V _{GS} = 0		1	mA
V _{SD}	Diode Forward Voltage	I _F = 14A; V _{GS} = 0		1.8	V